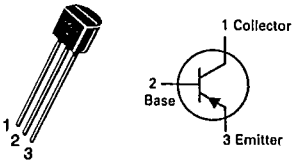
BC415, B, C
BC416, B, C

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



LOW NOISE TRANSISTORS

PNP SILICON

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MAXIMUM RATINGS

Rating	Symbol	BC 415	BC 416	Unit
Collector-Emitter Voltage	V_{CEO}	35	45	Vdc
Collector-Base Voltage	V_{CBO}	45	50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	100		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0) BC415 BC416	$V_{(BR)CEO}$	35 45			Vdc
Collector-Base Breakdown Voltage (I_C = 10 µAdc, I_E = 0) BC415 BC416	$V_{(BR)CBO}$	45 50			Vdc
Emitter-Base Breakdown Voltage (I_E = 10 µAdc, I_C = 0)	$V_{(BR)EBO}$	5			Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0) (V_{CB} = 30 Vdc, I_E = 0, T_A = +125°C)	I_{CBO}			15 5	nAdc µAdc
Emitter Cutoff Current (V_{EB} = 4 Vdc, I_C = 0)	I_{EBO}			15	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 10 µAdc, V_{CE} = 5 Vdc) BC415B/BC416B BC415C/BC416C (I_C = 2 mAdc, V_{CE} = 5 Vdc) BC415B/BC416B BC415C/BC416C BC415/BC416	h_{FE}	100 100 180 380 120	150 270 290 500 350	 460 800 800	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc) (I_C = 10 mAdc, I_B = see note 1) (I_C = 100 mAdc, I_B = 5 mAdc, see note 2)	$V_{CE(sat)}$		0.075 0.3 0.25	0.25 0.6	Vdc
Base-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 5 mAdc)	$V_{BE(sat)}$		1.1		Vdc
Base-Emitter On Voltage (I_C = 10 µAdc, V_{CE} = 5 Vdc) (I_C = 100 µAdc, V_{CE} = 5 Vdc) (I_C = 2 mAdc, V_{CE} = 5 Vdc)	$V_{BE(on)}$	 0.55	0.52 0.55 0.62	 0.75	Vdc
SMALL SIGNAL CHARACTERISTICS					
Current-Gain-Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5 Vdc, f = 100 MHz)	f_T		250		MHz
Collector-Base Capacitance (V_{CE} = 10 Vdc, I_E = 0, f = 1 MHz)	C_{cbo}		2.5		pF
Noise Figure (I_C = 200 µAdc, V_{CE} = 5 Vdc, R_S = 2 KΩ, f = 30 Hz – 15 KHz)	NF		0.5	2.0	dB

Note 1: I_B is value for which I_C = 11 mA at V_{CE} = 1 V

Note 2: Pulse test = 300 µs – Duty cycle = 2%